

This Page Is Inserted by IFW Operations  
and is not a part of the Official Record

## **BEST AVAILABLE IMAGES**

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

**IMAGES ARE BEST AVAILABLE COPY.**

**As rescanning documents *will not* correct images,  
please do not report the images to the  
Image Problem Mailbox.**

FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
SEMICONDUCTOR STRUCTURE FABRICATED THEREBY

Docket No. 2336-254

Inventor: Sun Woon KIM et al.

Page 1 of 5

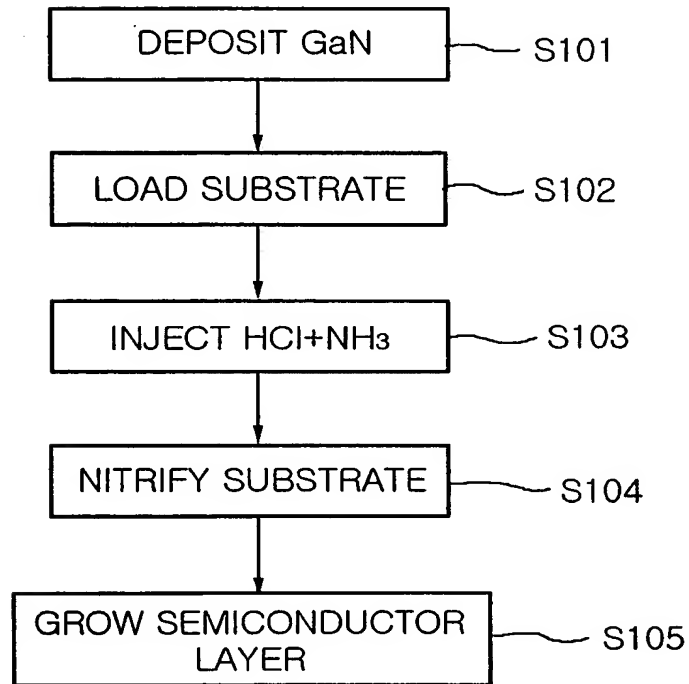


FIG. 1

FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
SEMICONDUCTOR STRUCTURE FABRICATED THEREBY

Docket No. 2336-254

Inventor: Sun Woon KIM et al.

Page 2 of 5

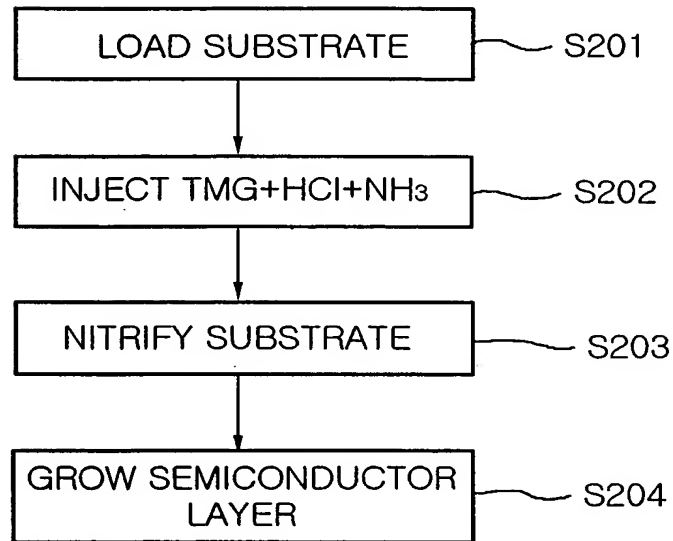


FIG. 2

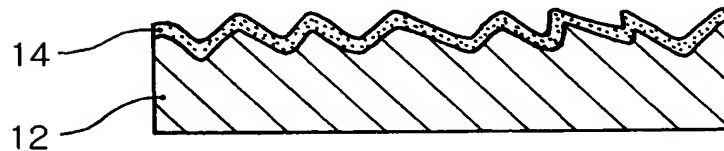


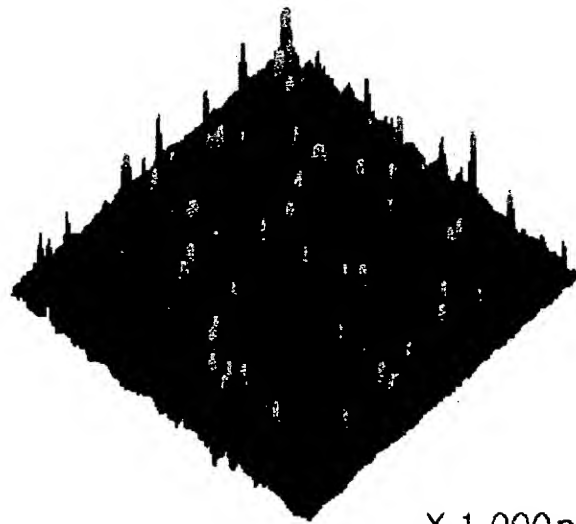
FIG. 3

FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
SEMICONDUCTOR STRUCTURE FABRICATED THEREBY

Docket No. 2336-254

Inventor: Sun Woon KIM et al.

*Page 3 of 5*



X 1.000nm /div  
Z 20.000nm /div

FIG. 4

FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
SEMICONDUCTOR STRUCTURE FABRICATED THEREBY

Docket No. 2336-254

Inventor: Sun Woon KIM et al.

Page 4 of 5

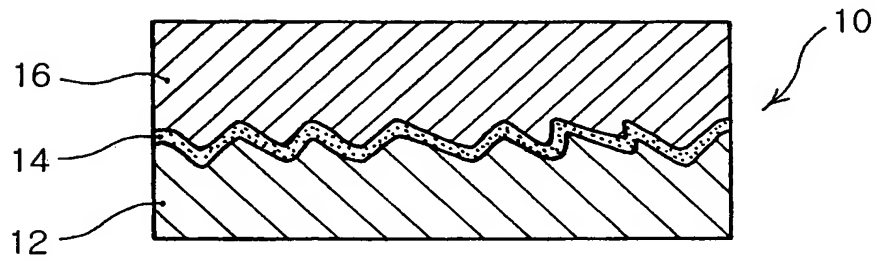
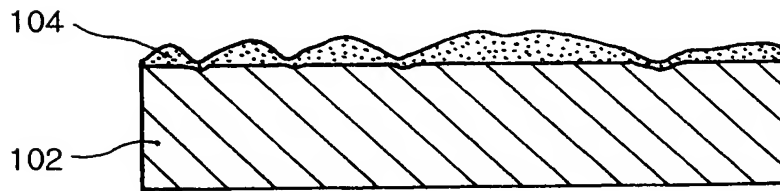


FIG. 5



PRIOR ART

FIG. 6

FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
SEMICONDUCTOR STRUCTURE FABRICATED THEREBY

Docket No. 2336-254

Inventor: Sun Woon KIM et al.

*Page 5 of 5*

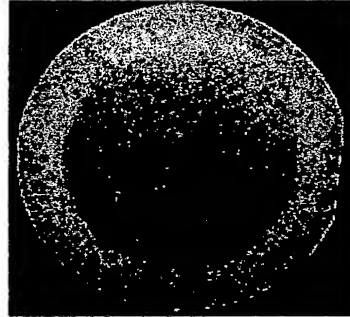
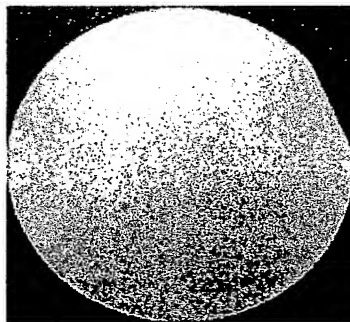
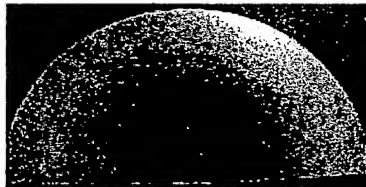


FIG. 7



PRIOR ART

FIG. 8



PRIOR ART

FIG. 9